IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application.

1 (Original). A semiconductor device comprising:

a first conductive film formed over an insulating substrate;

an inorganic insulating film covering said first conductive film;

an organic resin film covering said inorganic insulating film;

a contact hole that goes through said inorganic insulating film and said organic resin film; and

a second conductive film formed over said organic resin film and connected to said first conductive film at a bottom surface of said contact hole.

2 (Original). A device according to claim 1, wherein said contact hole is formed by performing one etching.

3 (Original). A device according to claim 1, wherein an edge portion of said inorganic insulating film that comes in contact with a bottom surface of said contact hole is taper like having an angle range of 30° to 80° from a horizontal surface.

4 (Original). A device according to claim 1, wherein an edge portion of said organic resin film that comes in contact with said inorganic insulating film has an angle range of 50° to 90° from a horizontal surface.

5 (Original). A device according to claim 1, further comprising a thin film transistor electrically connected to said first conductive film.

6 (Original). A device according to claim 1, wherein said second conductive film is a pixel electrode.

7 (Original). A device according to claim 1, wherein said inorganic insulating film is a silicon nitride film or a silicon oxide nitride film.

8 (Original). A device according to claim 1, wherein said semiconductor device includes an active matrix liquid crystal display device, an active matrix EL display device or an active matrix EC display device.

9 (Original). A device according to claim 1, wherein said semiconductor device includes a video camera, a digital camera, a projector, a goggle-type display, a navigation system for automobiles, a personal computer, and a mobile information terminal.

10-13 (Canceled).

14 (New). A semiconductor device comprising:

a substrate;

a source region and a drain region which are provided over said substrate with a channel region provided over said substrate between said source region and said drain region;

a gate electrode provided over said substrate and provided adjacent to said channel region with a gate insulating film between said gate electrode and said channel region;

a wiring provided over and connected with one of said source region and said drain region;

an inorganic insulating film provided over said wiring;

an organic resin film provided over said inorganic insulating film;

a contact hole provided through said inorganic insulating film and said organic resin film; and

a pixel electrode provided over said organic resin film and connected with said wiring through said contact hole.

15 (New). A device according to claim 14, wherein an edge portion of said inorganic insulating film that comes in contact with a bottom surface of said contact hole is taper like having an angle range of 30° to 80°from a horizontal surface.

16 (New). A device according to claim 14, wherein an edge portion of said organic resin film that comes in contact with said inorganic insulating film has an angle range of 50° to 90° from a horizontal surface.

17 (New). A device according to claim 14, wherein said inorganic insulating film is a silicon nitride film or a silicon oxide nitride film.

18 (New). A device according to claim 14, wherein said semiconductor device includes an

active matrix liquid crystal display device, an active matrix EL display device or an active matrix EC display device.

19 (New). A device according to claim 14, wherein said semiconductor device is incorporated into one selected from the group consisting of a video camera, a digital camera, a projector, a goggle-type display, a navigation system for automobiles, a personal computer, and a mobile information terminal.